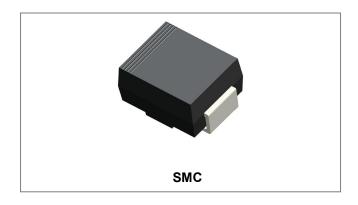






SK56 SCHOTTKY RECTIFIER



Features

- Small foot print, surface mountable
- Very low forward Voltage Drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Green Products in Compliance the ROHS Directive
- This is a Pb Free Device
- . All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Applications

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	-	60	V
Average Rectified Forward Current	I _{F (AV)}	50% duty cycle @T _C =105°C, rectangular wave form	5	Α
Peak Repetitive Forward Current	I _{FRM}	At Rated V _R , Square Wave, 20KHZ, T _C =80°C	10	Α
Peak One Cycle Non-Repetitive Surge Current	I _{FSM}	8.3ms, Half Sine pulse, T _c = 25 °C	125	Α

Electrical Characteristics:

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop*	V _{F1}	@ 5A, Pulse, T _J = 25 °C	0.58	0.70	V
	V _{F2}	@ 5A, Pulse, T _J = 125 °C	0.50	0.64	V
Reverse Current*	I _{R1}	$@V_R = \text{rated } V_{R_1} T_J = 25 ^{\circ}\text{C}$	0.02	1.0	mA
	I _{R2}	$@V_R = \text{rated } V_{R_1} T_J = 125 ^{\circ}\text{C}$	12	20	mA
Junction Capacitance	Ст	@V _R = 5V, T _C = 25 °C, f _{SIG} = 1MHz	170	400	pF
Series Inductance	Ls	Measured lead to lead 5 mm from package body	8.0	-	nH
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

^{*} Pulse width < 300 µs, duty cycle < 2%

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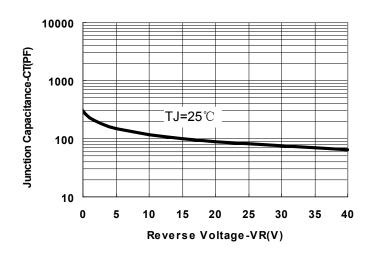




Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +150	°C
Storage Temperature	T _{stg}	-	-55 to +150	°C
Typical Thermal Resistance Junction to Lead	$R_{ heta JL}$	DC operation	20	°C/W
Typical Thermal Resistance Junction to Ambient	R _{θJA}	DC operation	84	°C/W
Approximate Weight	wt	-	0.09	g

Ratings and Characteristics Curves



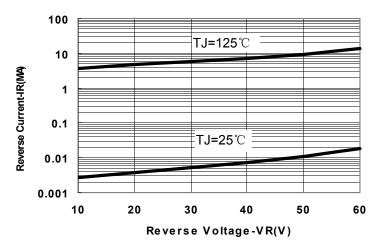


Fig.1-Typical Junction Capacitance

Fig.2-Typical Values Of Reverse Current

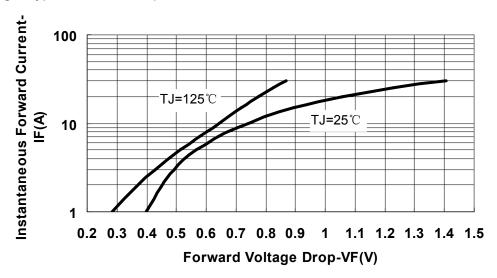


Fig.3-Typical Forward Voltage Drop Characteristics

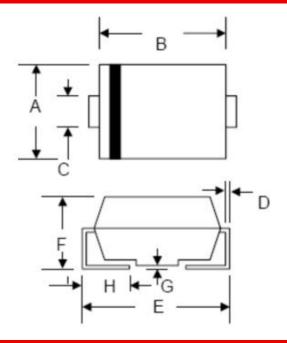
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Mechanical Dimensions SMC



SYMBOL	Millimeters		Inches		
	Min.	Max.	Min.	Max.	
Α	5.59	6.22	0.220	0.245	
В	6.60	7.11	0.260	0.280	
С	2.75	3.25	0.108	0.128	
D	0.152	0.305	0.006	0.012	
E	7.75	8.25	0.305	0.325	
F	2.00	2.95	0.079	0.116	
G	0.051	0.203	0.002	0.008	
Н	0.76	1.60	0.030	0.063	

Ordering Information

Device	Package	Shipping	
SK56	SMC (Pb-Free)	3000pcs / reel	

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Marking Diagram



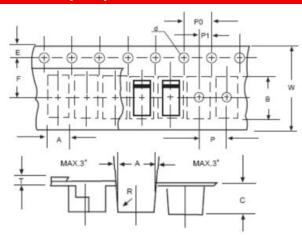
Where XXXXX is YYWWL

SK = Device Type 5 = Forward Current (5A) 6 = Reverse Voltage (60V)

YY = Year WW = Week L = Lot Number

Cautions: Molding resin Epoxy resin UL:94V-0

Carrier Tape Specification SMC



SYMBOL	Millimeters		
	Min.	Max.	
Α	5.90	6.10	
В	8.20	8.40	
C	2.40	2.60	
d	1.40	1.60	
E	1.40	1.60	
F	7.60	7.70	
Р	7.90	8.10	
P0	3.90	4.10	
P1	3.90	4.10	
Т	-	0.600	
W	15.80	16.20	

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